JIANGSU CHANGJIANG ELECTRONICS TECHNOLOGY CO., LTD

SOT-23 Plastic-Encapsulate Transistors

S9015 TRANSISTOR (PNP)

SOT-23



1. BASE
2. EMITTER
3. COLLECTOR

FEATURES

- **Complementary to S9014**

MARKING: M6

MAXIMUM RATINGS (T_A=25℃ unless otherwise noted)

Symbol	Parameter	Value	Units
V_{CBO}	Collector-Base Voltage	-50	V
V_{CEO}	Collector-Emitter Voltage	-45	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current -Continuous	-0.1	A
P_C	Collector Power Dissipation	0.2	W
T_j	Junction Temperature	150	℃
T_{stg}	Storage Temperature	-55-150	℃

ELECTRICAL CHARACTERISTICS (Tamb=25℃ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	I_C= -100μA, I_E=0	-50			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	I_C = -0.1mA, I_B=0	-45			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	I_E=-100μA, I_C=0	-5			V
Collector cut-off current	I_{CBO}	V_{CB}=-50 V, I_E=0			-0.1	μA
Emitter cut-off current	I_{EBO}	V_{EB}= -5V, I_C=0			-0.1	μA
DC current gain	h_{FE}	V_{CE}=-5V, I_C= -1mA	200		1000	
Collector-emitter saturation voltage	V_{CE}(sat)	I_C=-100mA, I_B= -10mA			-0.3	V
Base-emitter saturation voltage	V_{BE}(sat)	I_C=-100mA, I_B=-10mA			-1	V
Transition frequency	f_T	V_{CE}=-5V, I_C= -10mA f=30MHz	150			MHz

CLASSIFICATION OF h_{FE}

Rank	L	H
Range	200-450	450-1000

Typical Characteristics S9015

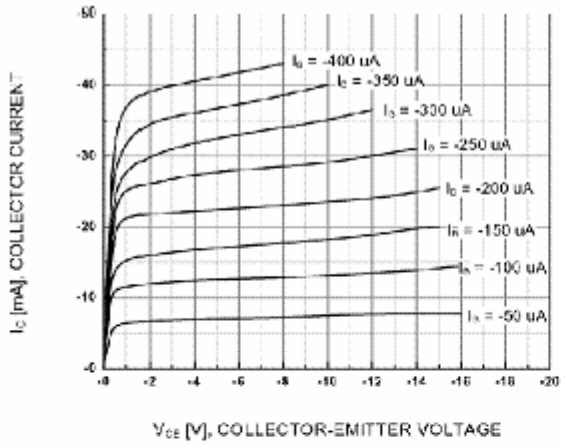

Figure 1. Static Characteristic

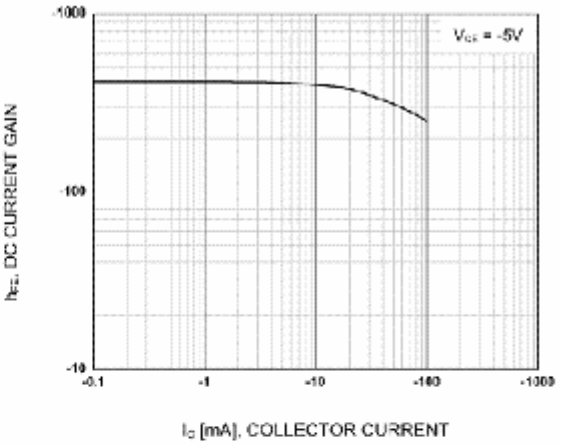

Figure 2. DC current Gain

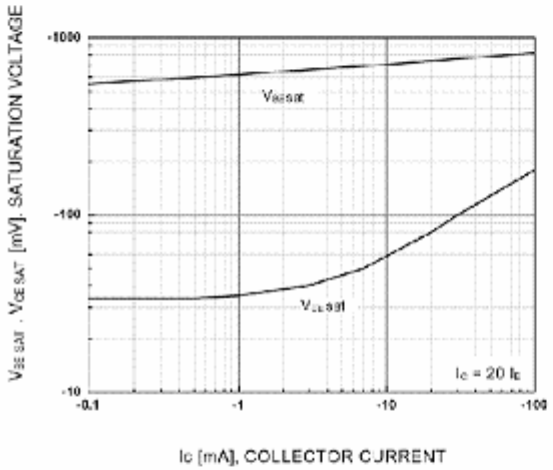

Figure 3. Base-Emitter Saturation Voltage Collector-Emitter Saturation Voltage

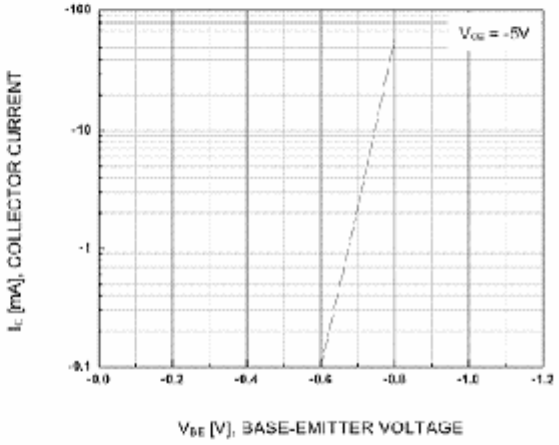

Figure 4. Base-Emitter On Voltage

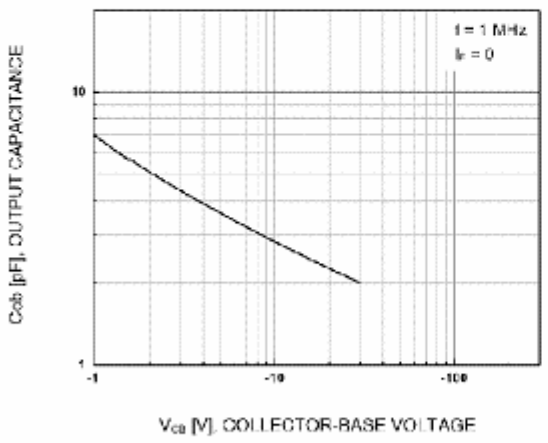

Figure 5. Collector Output Capacitance

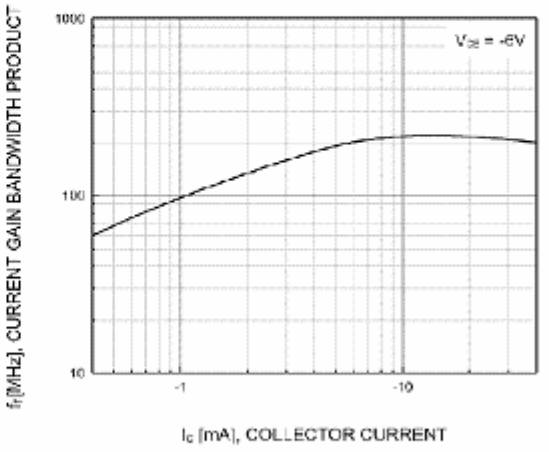

Figure 6. Current Gian Bandwidth Product